



40V N-Channel Enhancement Mode MOSFET

Voltage

40 V

Current

100A

Features

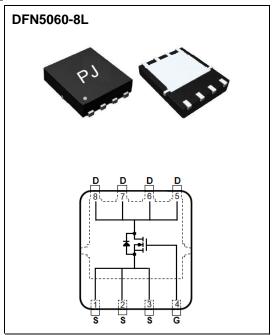
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@20A<2.8m\Omega$
- R_{DS(ON)}, V_{GS}@4.5V, I_D@12A<3.5mΩ
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN5060-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0028 ounces, 0.08 grams



Maximum Ratings and Thermal Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	40		
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T _C =25°C	l _D	100		
	T _C =100°C		64	Α	
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	400		
Power Dissipation	T _C =25°C	Po	83.3	107	
	T _C =100°C		41.7	W	
Continuous Drain Current (Note 4)	T _A =25°C	I _D	17		
	T _A =70°C		13	Α	
Power Dissipation	T _A =25°C	.	2.4	W	
	T _A =70°C	Pb	1.6		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	312	mJ	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~175	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	1.8	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1	1.54	2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	-	2.2	2.8	mΩ
		V _{GS} =4.5V, I _D =12A	-	2.6	3.5	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Q_g	V _{DS} =20V, I _D =10A, V _{GS} =4.5V (Note 2,3)	-	50	-	nC
Gate-Source Charge	Q_{gs}		-	13	-	
Gate-Drain Charge	Q_gd		-	19	-	
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V, f=1MHZ	-	5214	-	pF
Output Capacitance	Coss		-	492	-	
Reverse Transfer Capacitance	Crss	I= IIVIAZ	-	246	-	
Turn-On Delay Time	td _(on)	\/ 00\/ I 4A	-	44	-	
Turn-On Rise Time	t _r	$\begin{array}{c} V_{DS}{=}20V,\ I_{D}{=}1A,\\ V_{GS}{=}10V,\ R_{G}{=}6\Omega\\ \text{(Note 2,3)} \end{array}$	-	43	-	ns
Turn-Off Delay Time	td _(off)		-	218	-	
Turn-Off Fall Time	t _f		-	62	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	,		-	-	100	А
Diode Forward Current	I _S					
Diode Forward Voltage	V_{SD}	I _S =1A, V _{GS} =0V	-	0.65	1	V

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS}=79A, V_{DD}=25V, V_{GS}=10V, Starting T_J=25°C.
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

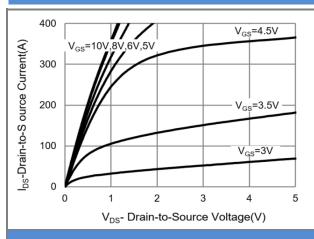


Fig.1 On-Region Characteristics

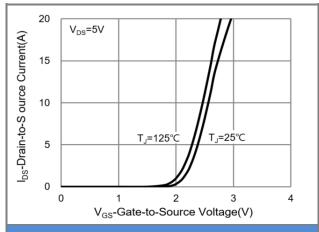


Fig.2 Transfer Characteristics

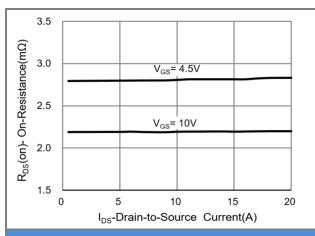


Fig.3 On-Resistance vs. Drain Current

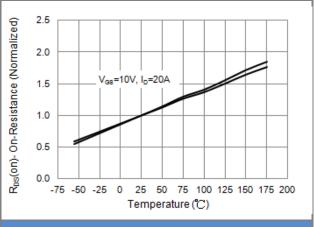


Fig.4 On-Resistance vs. Junction temperature

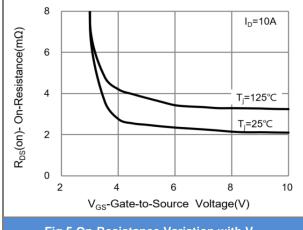


Fig.5 On-Resistance Variation with V_{GS}

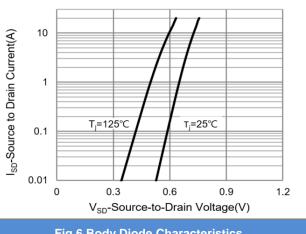


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

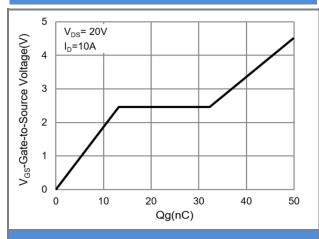


Fig.7 Gate-Charge Characteristics

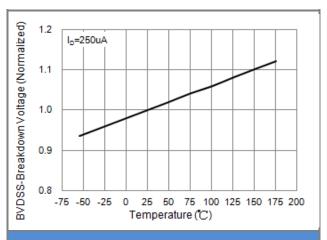


Fig.8 Breakdown Voltage Variation vs. Temperature

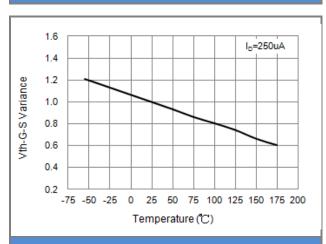


Fig.9 Threshold Voltage Variation with Temperature

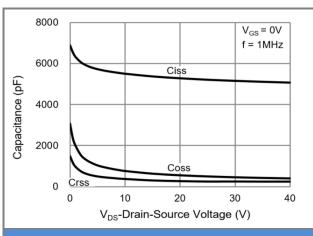


Fig.10 Capacitance vs. Drain-Source Voltage

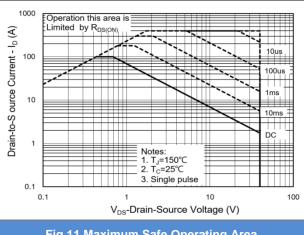


Fig.11 Maximum Safe Operating Area

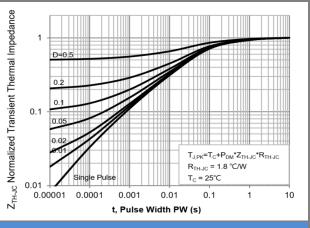


Fig.12 Normalized Transient Thermal Impedance

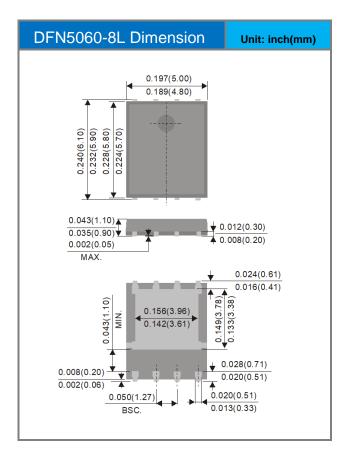


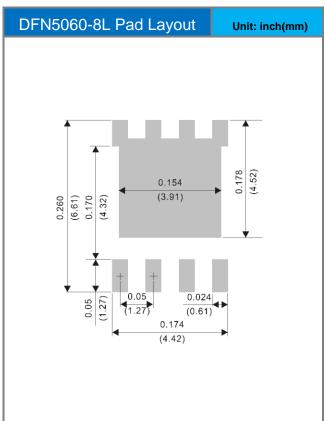


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ5440-AU_R2_000A1	DFN5060-8L	3000pcs / 13" reel	Q5440	Halogen free	

Packaging Information & Mounting Pad Layout





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